

Green Products

30BQ100 SCHOTTKY RECTIFIER

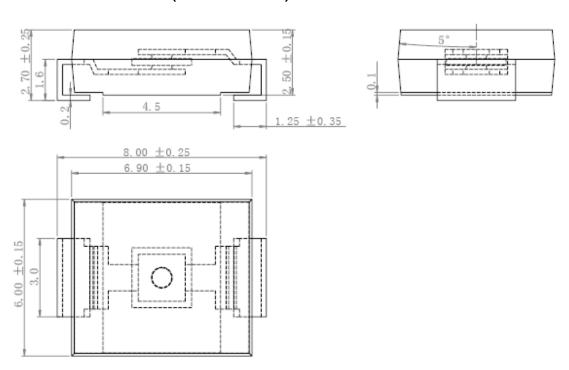
Applications:

- Disk Drives
- · Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Features:

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions (In mm / Inches):



SMC

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Marking Diagram:



Where XXXXX is YYWWL

 SC3J
 = Part Name

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
30BQ100	SMC (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =148°C, rectangular wave form	3.0	А
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	120	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 3 A, Pulse, T _J = 25 °C	0.79	V
		@ 6 A, Pulse, T _J = 25 °C	0.90	
	V_{F2}	@ 3 A, Pulse, T _J = 125 °C	0.62	V
		@ 6 A, Pulse, T _J = 125°C	0.70	
Max. Reverse Current *	I _{R1}	$@V_R = Rated V_R, Pulse,$	0.5	mA
		$T_J = 25 ^{\circ}C$		
	I _{R2}	$@V_R = Rated V_R, Pulse,$	5	mA
		$T_{J} = 125 ^{\circ}\text{C}$		
Max. Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$	115	PF
		$f_{SIG} = 1MHz$		
Typical Series Inductance	Ls	Measured lead to lead 5 mm from	3.0	nΗ
		package body		
Max. Voltage Rate of	dv/dt	-	10,000	V/μs
Change				

 $^{^*}$ Pulse Width < 300 μ s, Duty Cycle < 2%

Thermal-Mechanical Specifications:

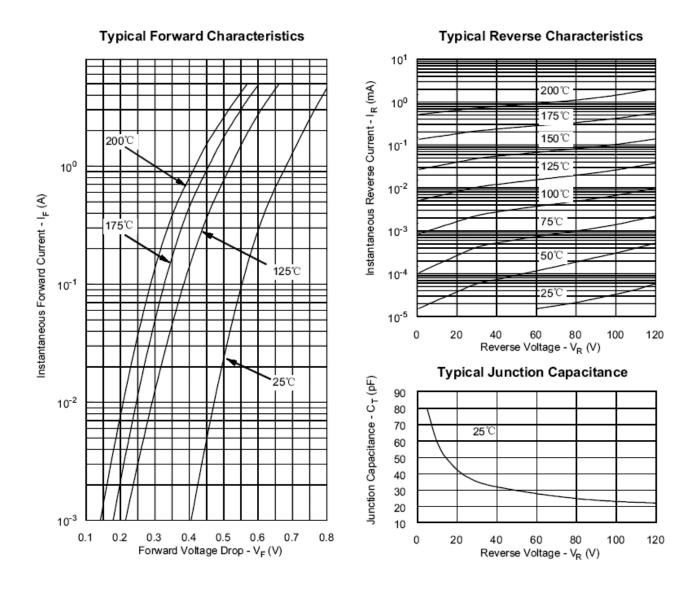
Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +175	°C
Max. Storage Temperature	T_{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Lead	$R_{ hetaJL}$	DC operation	12	°C/W
Maximum Thermal Resistance Junction to Case	$R_{ hetaJA}$	DC operation	46	°C/W
Approximate Weight	wt	-	0.65	g
Case Style		SMC		

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